

## 150V N-Channel Enhancement Mode MOSFET

### Description

The 30N15D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

$V_{DS} = 150V$   $I_D = 30A$

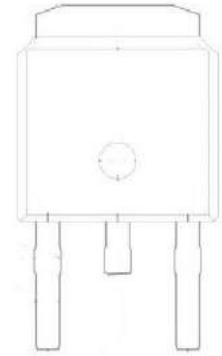
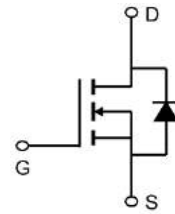
$R_{DS(ON)} < 52m\Omega$  @  $V_{GS}=10V$

### Application

Battery protection

Load switch

Uninterruptible power supply



### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	150	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current <sup>1</sup>	30	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current <sup>1</sup>	16	A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current <sup>1</sup>	4.5	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current <sup>1</sup>	3.8	A
IDM	Pulsed Drain Current <sup>2</sup>	60	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>3</sup>	72.6	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	2.7	W
TSTG	Storage Temperature Range	-55 to 175	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 175	°C
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	55	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	2.0	°C/W

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### Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

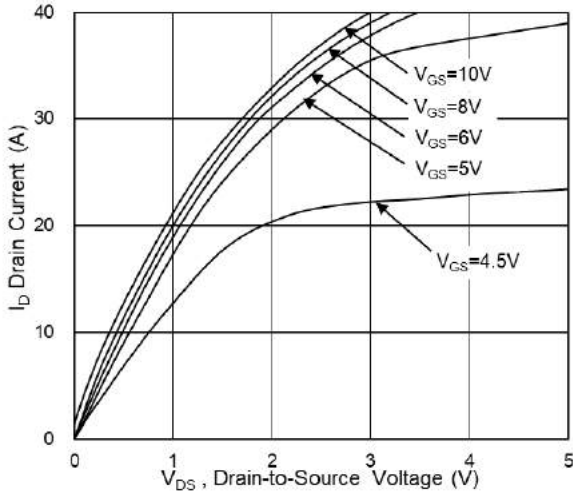
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	150	165	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=20A$	---	43	52	m $\Omega$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=10A$	---	45	70	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.8	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=120V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{DS}=120V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	25	---	S
$Q_g$	Total Gate Charge	$V_{DS}=75V, V_{GS}=10V, I_D=10A$	---	23	---	nC
$Q_{gs}$	Gate-Source Charge		---	5.8	---	
$Q_{gd}$	Gate-Drain Charge		---	4.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=75V, V_{GS}=10V, R_G=3.3\Omega, I_D=10A$	---	16.2	---	ns
$T_r$	Rise Time		---	18.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	28.5	---	
$T_f$	Fall Time		---	6.5	---	
$C_{iss}$	Input Capacitance	$V_{DS}=75V, V_{GS}=0V, f=1\text{MHz}$	---	1190	---	pF
$C_{oss}$	Output Capacitance		---	73	---	
$C_{rss}$	Reverse Transfer Capacitance		---	4	---	
$I_S$	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V, \text{Force Current}$	---	---	20	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=10A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	45	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	138	---	nC

Note :

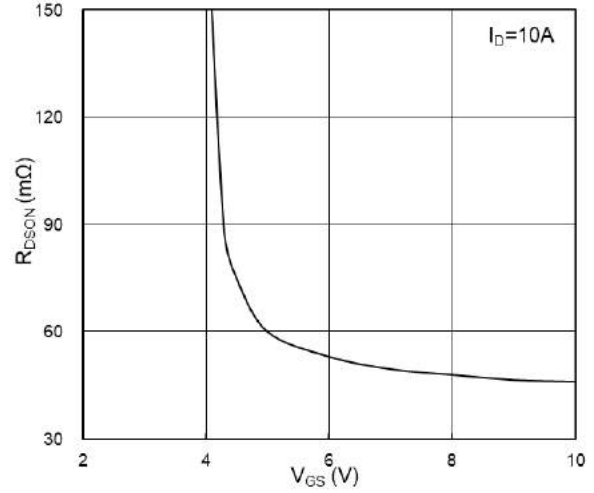
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by 150 $^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

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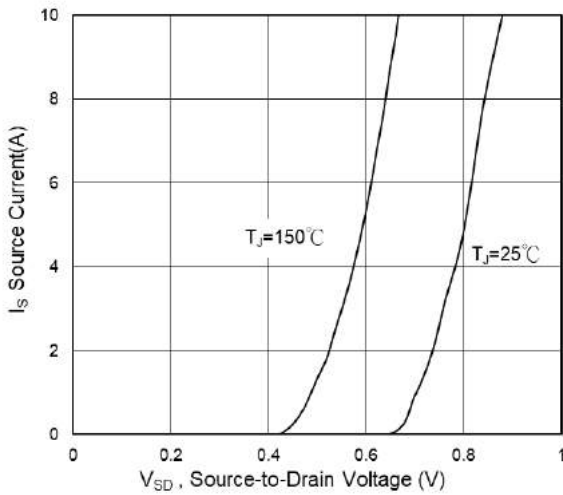
### Typical Characteristics



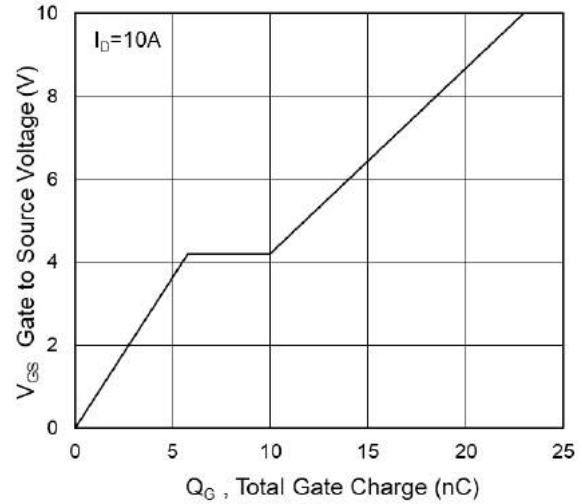
**Fig.1 Typical Output Characteristics**



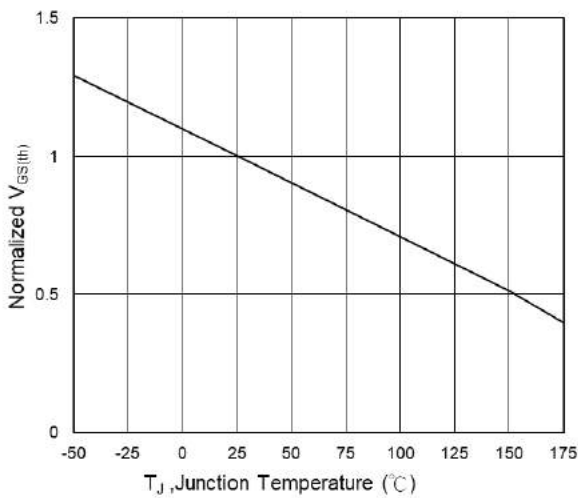
**Fig.2 On-Resistance vs G-S Voltage**



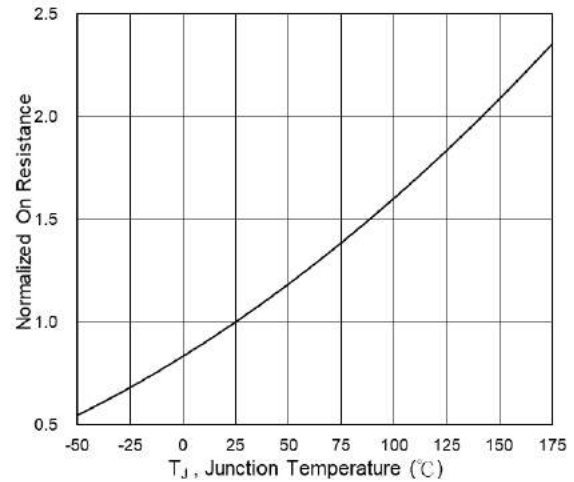
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



**Fig.6 Normalized  $R_{DSON}$  vs  $T_J$**

## 150V N-Channel Enhancement Mode MOSFET

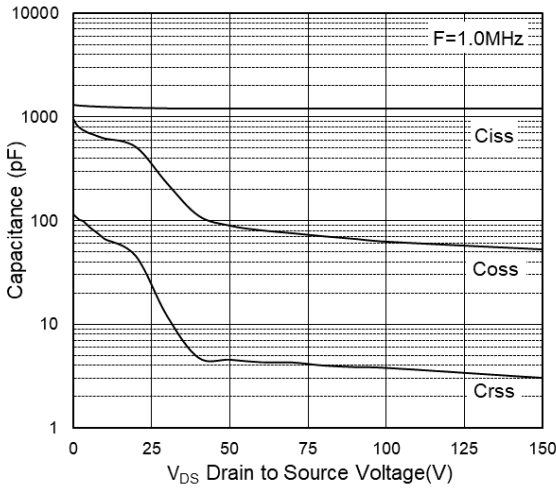


Fig.7 Capacitance

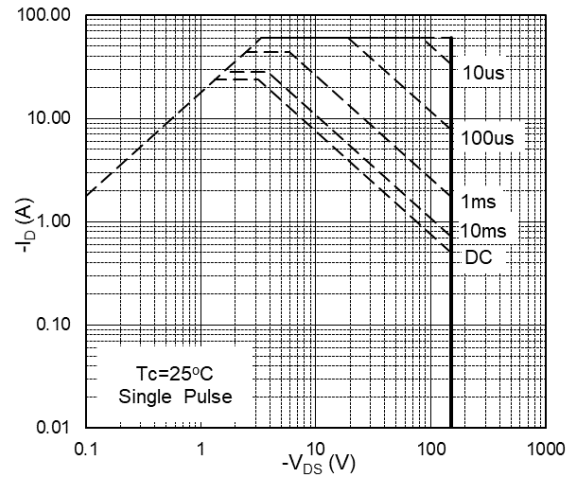


Fig.8 Safe Operating Area

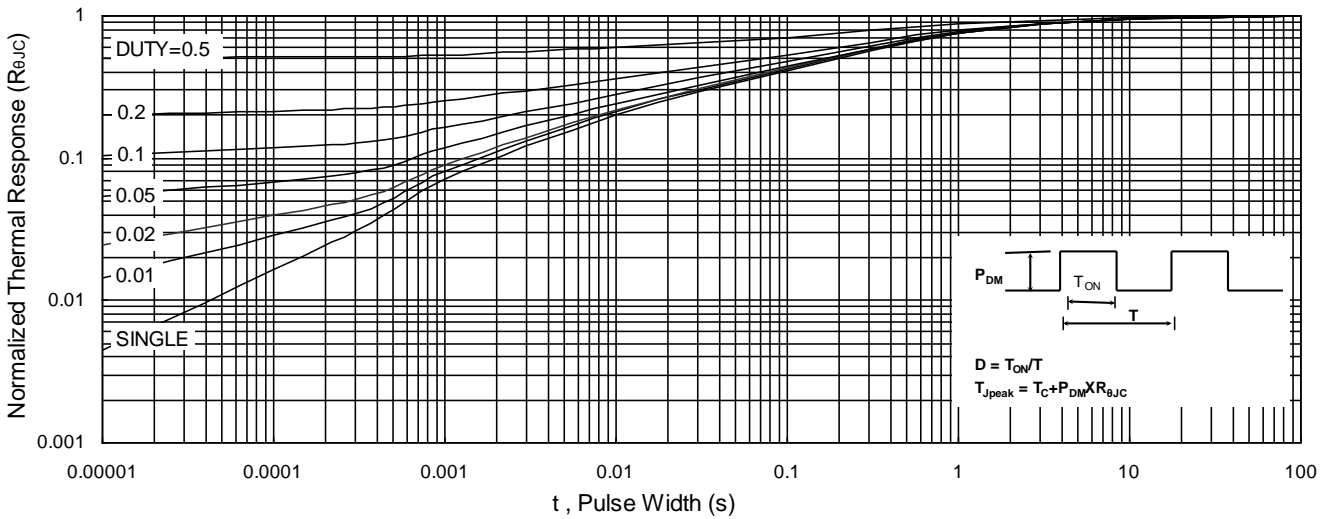


Fig.9 Normalized Maximum Transient Thermal Impedance

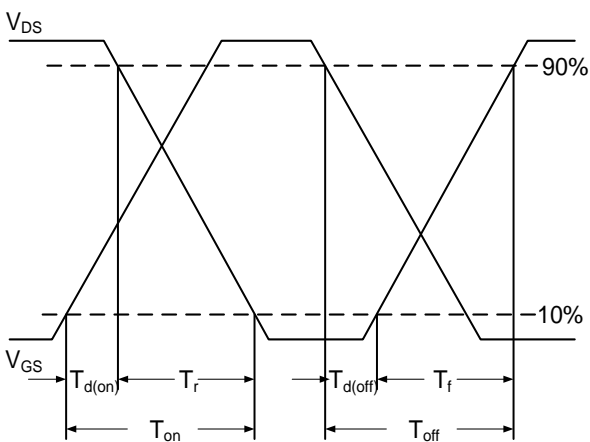


Fig.10 Switching Time Waveform

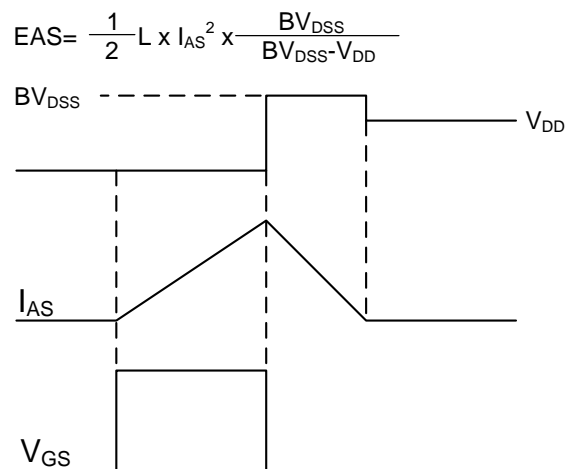
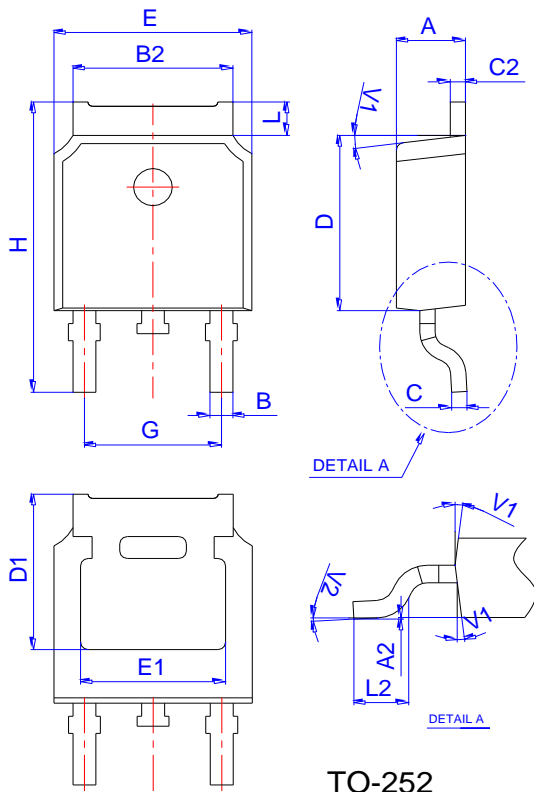


Fig.11 Unclamped Inductive Switching Waveform

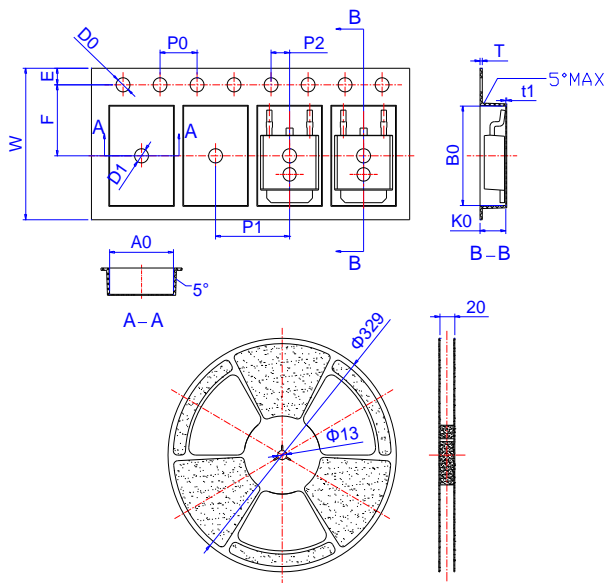
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### Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

### Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583